



YJB70G10B

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	70A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	8.6 mohm
$R_{DS(ON)}$ (at $V_{GS}=6V$)	13 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Low $R_{DS(on)}$ & FOM
Extremely low switching loss
Excellent stability and uniformity
Fast switching and soft recovery
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Power switching application
Hard switched and high frequency circuits
UPS

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter



Typical Performance Characteristics

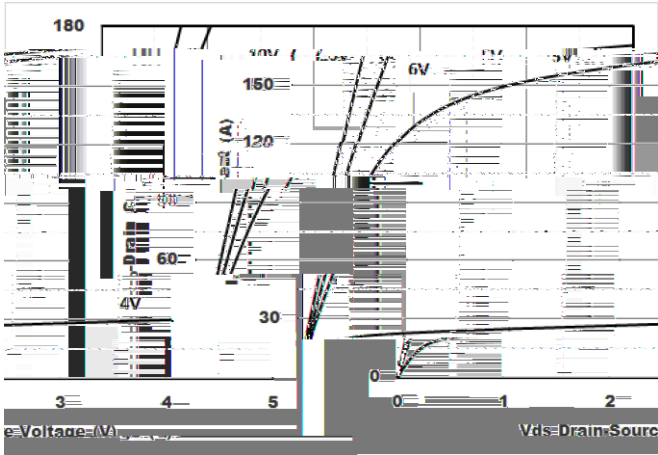


Figure1. Output Characteristics

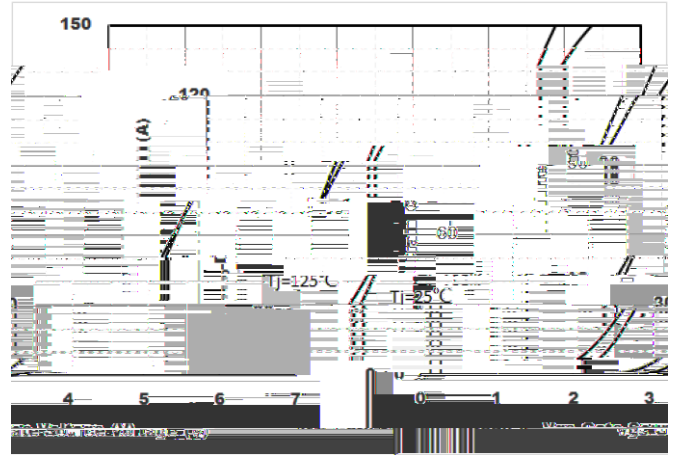


Figure2. Transfer Characteristics

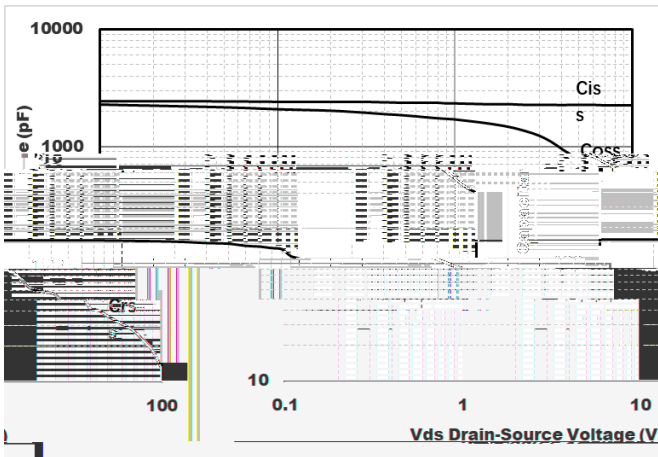


Figure3. Capacitance Characteristics

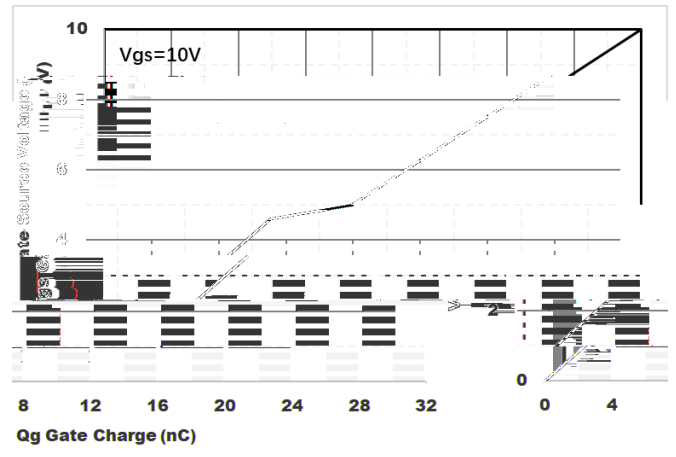


Figure4. Gate Charge

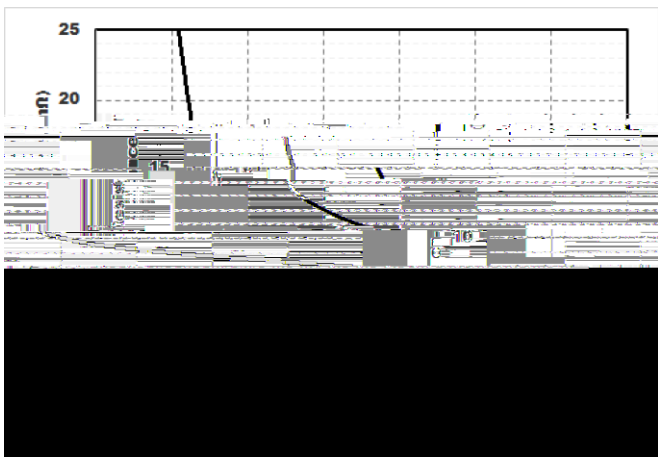


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

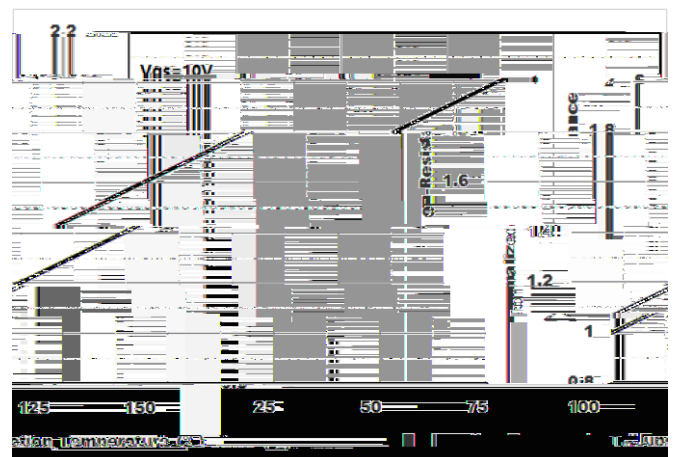


Figure6. Normalized On-Resistance



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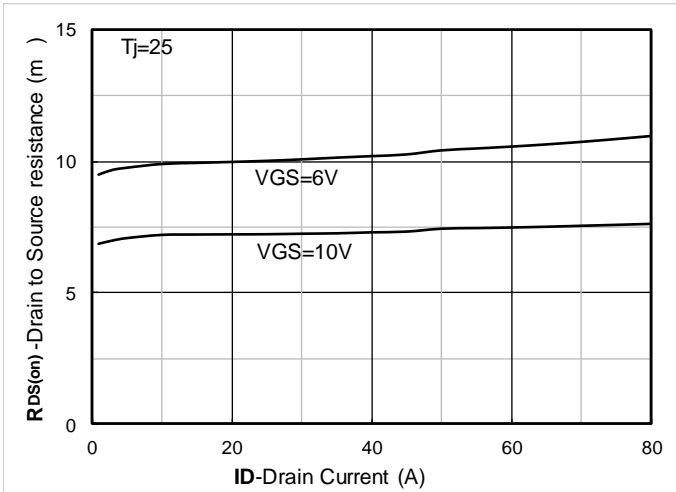


Figure 7. $R_{DS(on)}$ VS Drain Current

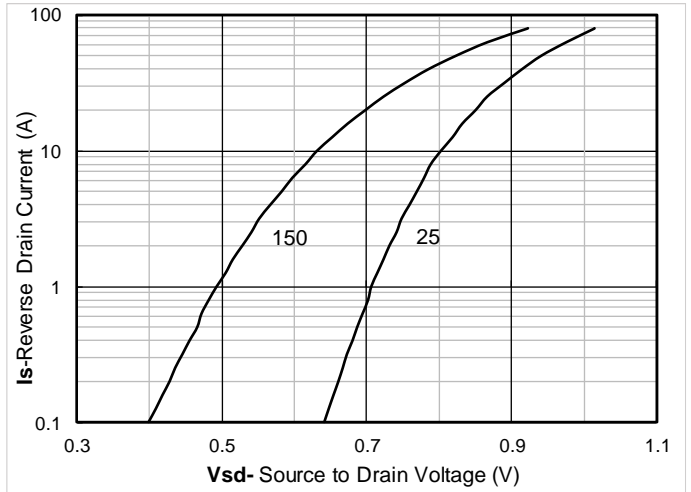


Figure 8. Forward characteristics of reverse diode

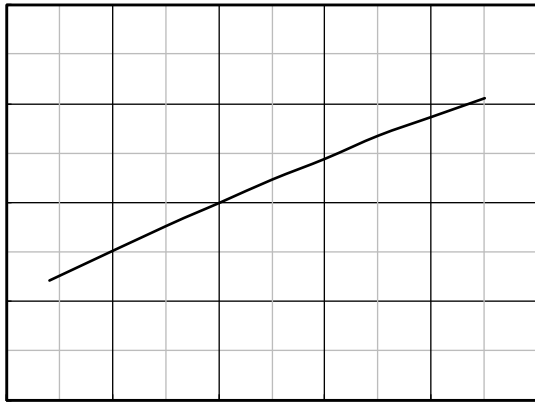
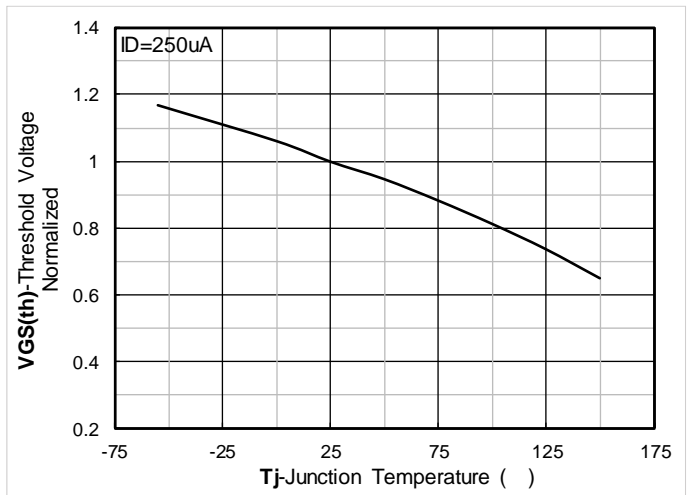


Figure 9. Normalized breakdown voltage





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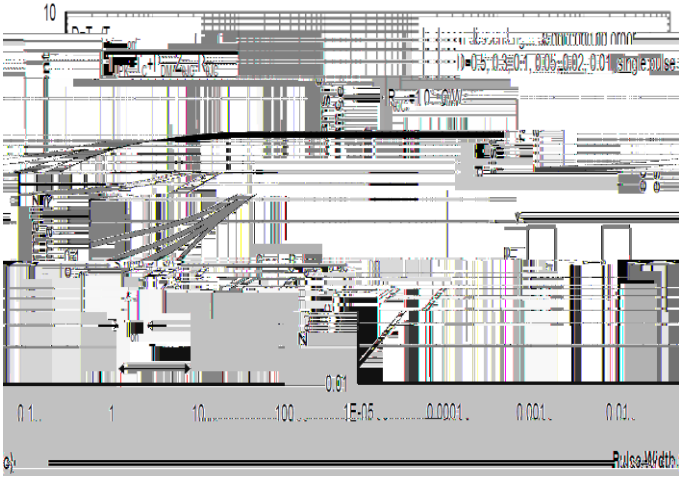


Figure 13. Normalized Maximum Transient thermal impedance

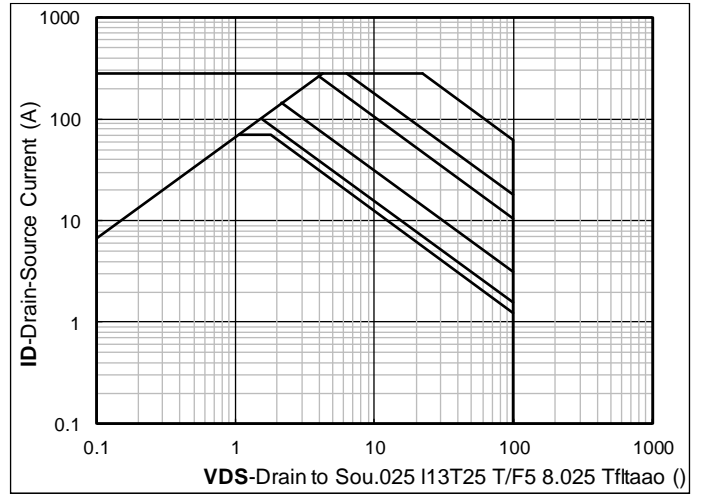


Figure 14. Safe Operation Area



TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E E1		



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Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as